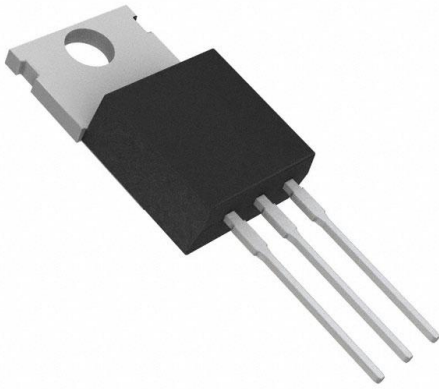


# TIP121G Datasheet

[www.digi-electronics.com](http://www.digi-electronics.com)



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	TIP121G-DG
Manufacturer	<a href="#">onsemi</a>
Manufacturer Product Number	TIP121G
Description	TRANS NPN DARL 80V 5A TO220
Detailed Description	Bipolar (BJT) Transistor NPN - Darlington 80 V 5 A 2 W Through Hole TO-220



Tel: +00 852-30501935

RFQ Email: [Info@DiGi-Electronics.com](mailto:Info@DiGi-Electronics.com)

DiGi is a global authorized distributor of electronic components.

## Purchase and inquiry

Manufacturer Product Number:

TIP121G

Series:

-

Transistor Type:

NPN - Darlington

Voltage - Collector Emitter Breakdown (Max):

80 V

Current - Collector Cutoff (Max):

500µA

Power - Max:

2 W

Operating Temperature:

-65°C ~ 150°C (TJ)

Package / Case:

TO-220-3

Base Product Number:

TIP121

Manufacturer:

onsemi

Product Status:

Active

Current - Collector (Ic) (Max):

5 A

Vce Saturation (Max) @ Ib, Ic:

4V @ 20mA, 5A

DC Current Gain (hFE) (Min) @ Ic, Vce:

1000 @ 3A, 3V

Frequency - Transition:

-

Mounting Type:

Through Hole

Supplier Device Package:

TO-220

## Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

Not Applicable

ECCN:

EAR99

# Plastic Medium-Power Complementary Silicon Transistors

## TIP120, TIP121, TIP122 (NPN); TIP125, TIP126, TIP127 (PNP)

Designed for general-purpose amplifier and low-speed switching applications.

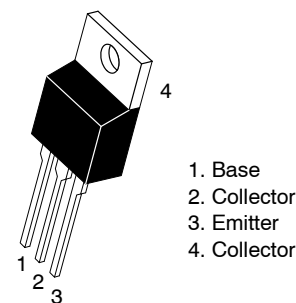
### Features

- High DC Current Gain –
 
$$h_{FE} = 2500 \text{ (Typ) @ } I_C = 4.0 \text{ Adc}$$
- Collector–Emitter Sustaining Voltage – @ 100 mAdc
 
$$V_{CEO(sus)} = 60 \text{ Vdc (Min) – TIP120, TIP125}$$

$$= 80 \text{ Vdc (Min) – TIP121, TIP126}$$

$$= 100 \text{ Vdc (Min) – TIP122, TIP127}$$
- Low Collector–Emitter Saturation Voltage –
 
$$V_{CE(sat)} = 2.0 \text{ Vdc (Max) @ } I_C = 3.0 \text{ Adc}$$

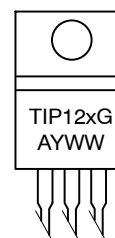
$$= 4.0 \text{ Vdc (Max) @ } I_C = 5.0 \text{ Adc}$$
- Monolithic Construction with Built-In Base–Emitter Shunt Resistors
- Pb–Free Packages are Available\*



TO-220AB  
CASE 221A  
STYLE 1

## DARLINGTON 5 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 60–80–100 VOLTS, 65 WATTS

### MARKING DIAGRAM



TIP12x	= Device Code
x	= 0, 1, 2, 5, 6, or 7
A	= Assembly Location
Y	= Year
WW	= Work Week
G	= Pb–Free Package

### ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet.

\*For additional information on our Pb–Free strategy and soldering details, please download the [onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D](#).

**TIP120, TIP121, TIP122 (NPN); TIP125, TIP126, TIP127 (PNP)****MAXIMUM RATINGS**

Symbol	Rating	TIP120, TIP125	TIP121, TIP126	TIP122, TIP127	Unit
$V_{CEO}$	Collector–Emitter Voltage	60	80	100	Vdc
$V_{CB}$	Collector–Base Voltage	60	80	100	Vdc
$V_{EB}$	Emitter–Base Voltage	5.0			Vdc
$I_C$	Collector Current – Continuous – Peak	5.0 8.0			Adc
$I_B$	Base Current	120			mAdc
$P_D$	Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	65 0.52			W W/ $^\circ\text{C}$
$P_D$	Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	2.0 0.016			W W/ $^\circ\text{C}$
E	Unclamped Inductive Load Energy (Note 1)	50			mJ
$T_J, T_{stg}$	Operating and Storage Junction, Temperature Range	–65 to +150			$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

**THERMAL CHARACTERISTICS**

Symbol	Characteristic	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction–to–Case	1.92	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction–to–Ambient	62.5	$^\circ\text{C}/\text{W}$

1.  $I_C = 1\text{ A}$ ,  $L = 100\text{ mH}$ , P.R.F. = 10 Hz,  $V_{CC} = 20\text{ V}$ ,  $R_{BE} = 100\ \Omega$

**ELECTRICAL CHARACTERISTICS** ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

Symbol	Characteristic	Min	Max	Unit
--------	----------------	-----	-----	------

**OFF CHARACTERISTICS**

$V_{CEO(sus)}$	Collector–Emitter Sustaining Voltage (Note 2) ( $I_C = 100\text{ mAdc}$ , $I_B = 0$ )	TIP120, TIP125 TIP121, TIP126 TIP122, TIP127	60 80 100	– – –	Vdc
$I_{CEO}$	Collector Cutoff Current ( $V_{CE} = 30\text{ Vdc}$ , $I_B = 0$ ) ( $V_{CE} = 40\text{ Vdc}$ , $I_B = 0$ ) ( $V_{CE} = 50\text{ Vdc}$ , $I_B = 0$ )	TIP120, TIP125 TIP121, TIP126 TIP122, TIP127	– – –	0.5 0.5 0.5	mAdc
$I_{CBO}$	Collector Cutoff Current ( $V_{CB} = 60\text{ Vdc}$ , $I_E = 0$ ) ( $V_{CB} = 80\text{ Vdc}$ , $I_E = 0$ ) ( $V_{CB} = 100\text{ Vdc}$ , $I_E = 0$ )	TIP120, TIP125 TIP121, TIP126 TIP122, TIP127	– – –	0.2 0.2 0.2	mAdc
$I_{EBO}$	Emitter Cutoff Current ( $V_{BE} = 5.0\text{ Vdc}$ , $I_C = 0$ )		–	2.0	mAdc

**ON CHARACTERISTICS** (Note 2)

$h_{FE}$	DC Current Gain ( $I_C = 0.5\text{ Adc}$ , $V_{CE} = 3.0\text{ Vdc}$ ) ( $I_C = 3.0\text{ Adc}$ , $V_{CE} = 3.0\text{ Vdc}$ )	1000 1000	– –	–
$V_{CE(sat)}$	Collector–Emitter Saturation Voltage ( $I_C = 3.0\text{ Adc}$ , $I_B = 12\text{ mAdc}$ ) ( $I_C = 5.0\text{ Adc}$ , $I_B = 20\text{ mAdc}$ )	– –	2.0 4.0	Vdc
$V_{BE(on)}$	Base–Emitter On Voltage ( $I_C = 3.0\text{ Adc}$ , $V_{CE} = 3.0\text{ Vdc}$ )	–	2.5	Vdc

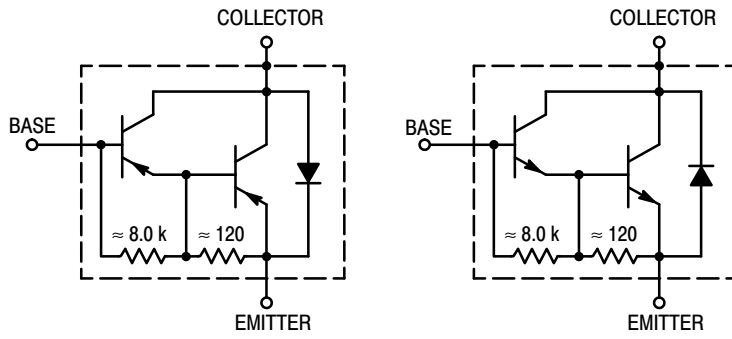
**DYNAMIC CHARACTERISTICS**

$h_{fe}$	Small–Signal Current Gain ( $I_C = 3.0\text{ Adc}$ , $V_{CE} = 4.0\text{ Vdc}$ , $f = 1.0\text{ MHz}$ )	4.0	–	–	
$C_{ob}$	Output Capacitance ( $V_{CB} = 10\text{ Vdc}$ , $I_E = 0$ , $f = 0.1\text{ MHz}$ )	TIP125, TIP126, TIP127 TIP120, TIP121, TIP122	– –	300 200	pF

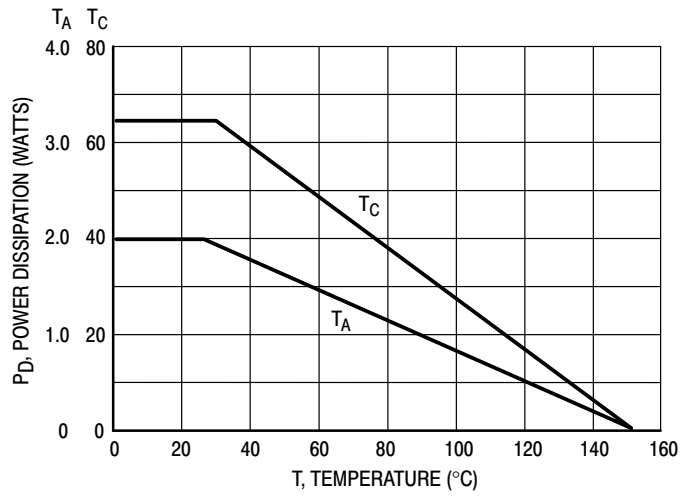
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2\%$

**TIP120, TIP121, TIP122 (NPN); TIP125, TIP126, TIP127 (PNP)**



**Figure 1. Darlington Circuit Schematic**



**Figure 2. Power Derating**

**TIP120, TIP121, TIP122 (NPN); TIP125, TIP126, TIP127 (PNP)**

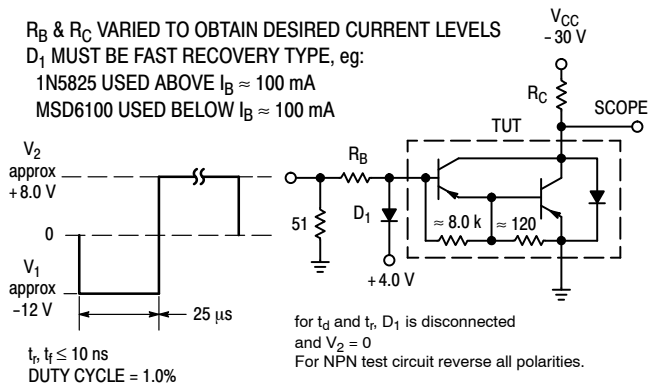


Figure 3. Switching Times Test Circuit

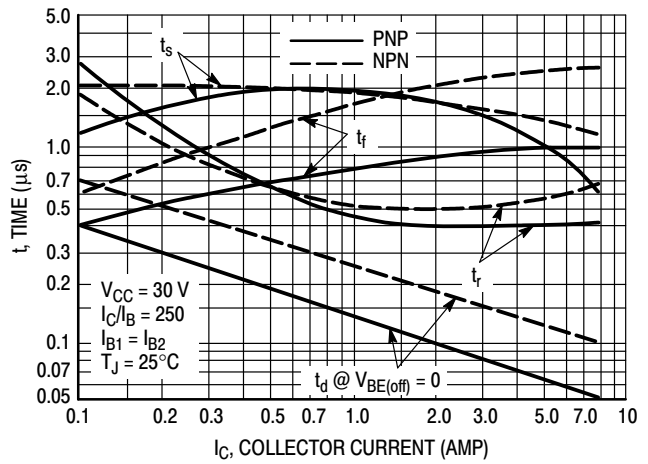


Figure 4. Switching Times

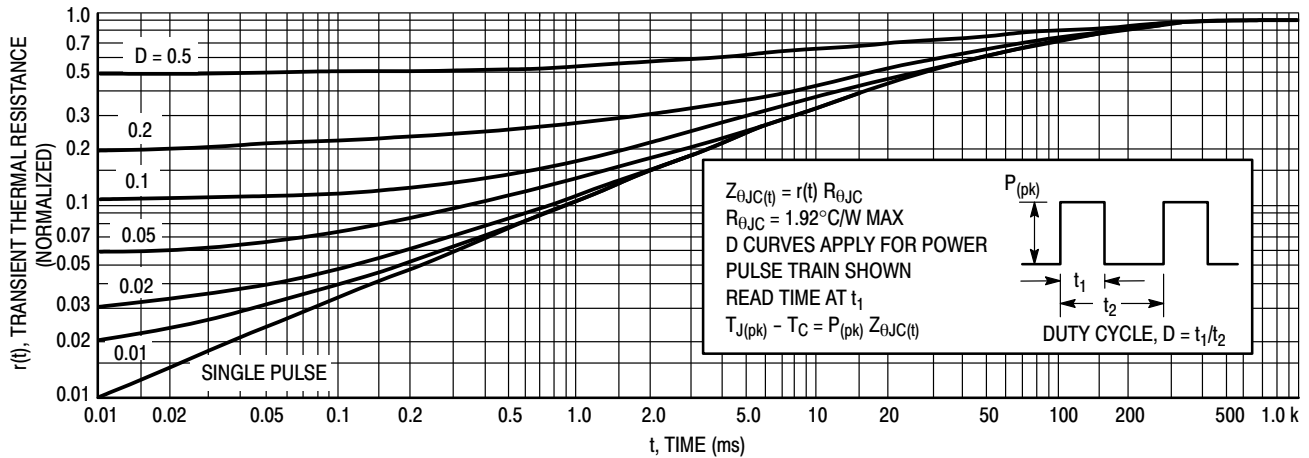
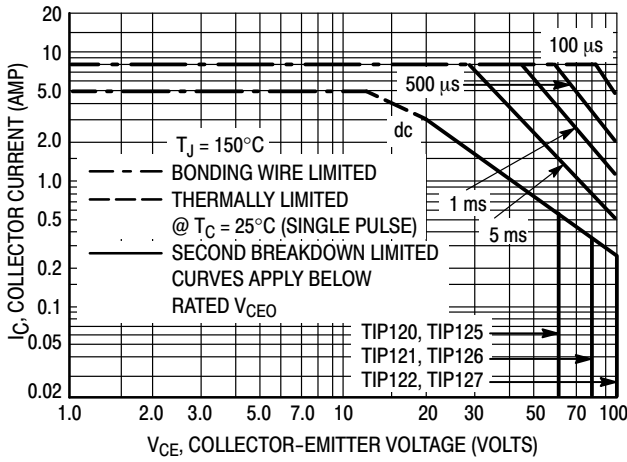


Figure 5. Thermal Response

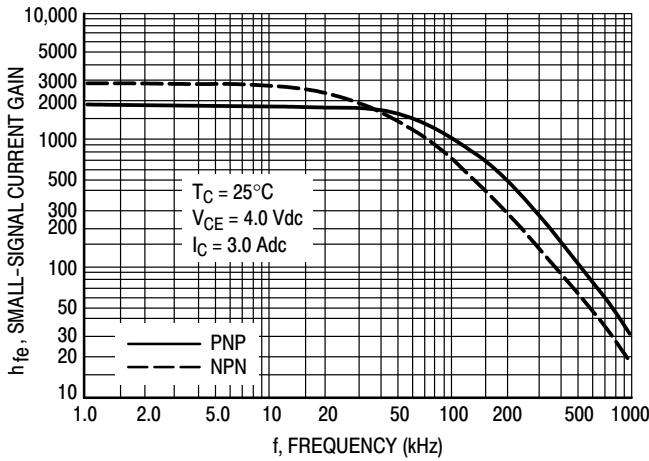
**TIP120, TIP121, TIP122 (NPN); TIP125, TIP126, TIP127 (PNP)**



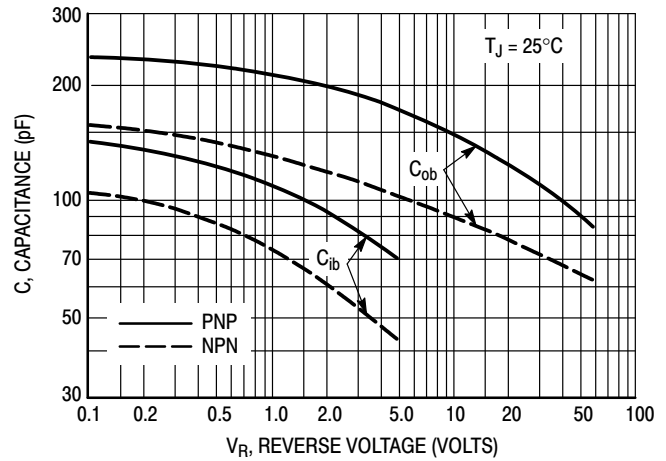
**Figure 6. Active-Region Safe Operating Area**

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 6 is based on  $T_{J(pk)} = 150^\circ\text{C}$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} < 150^\circ\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 5. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown

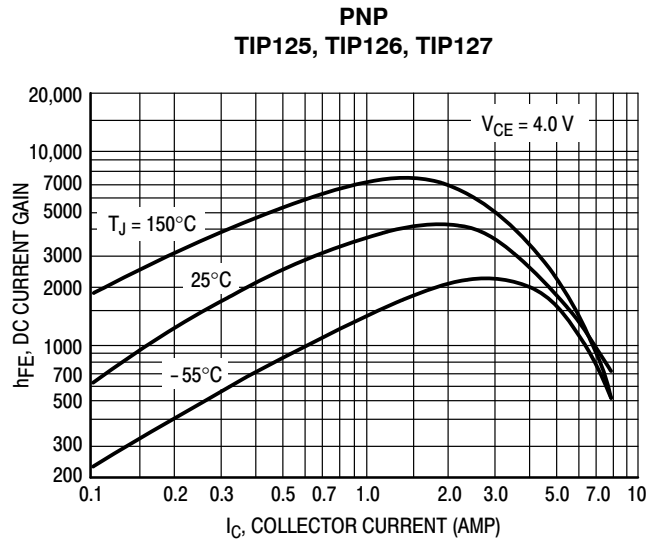
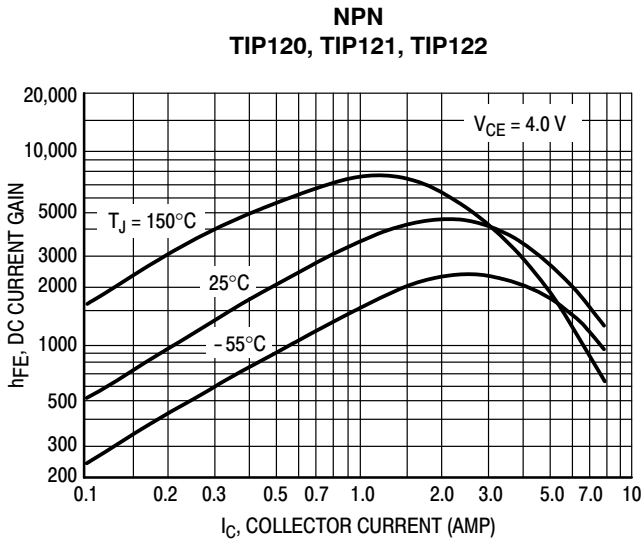


**Figure 7. Small-Signal Current Gain**

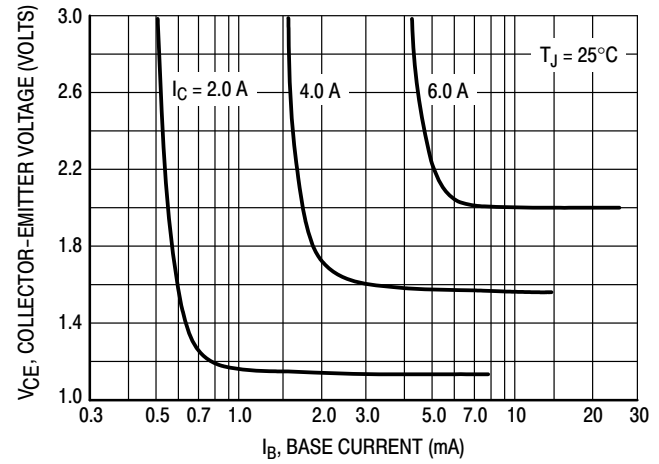
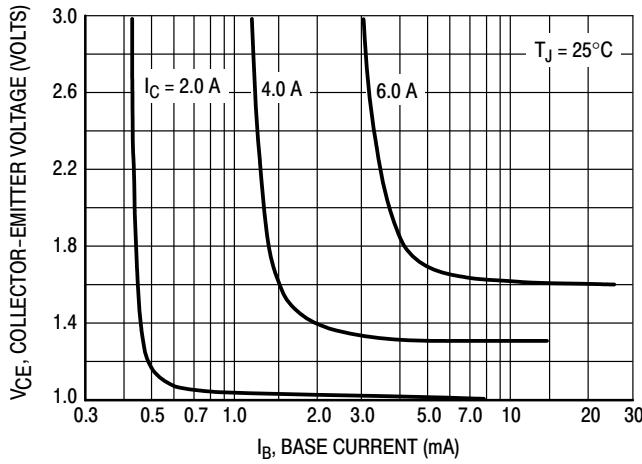


**Figure 8. Capacitance**

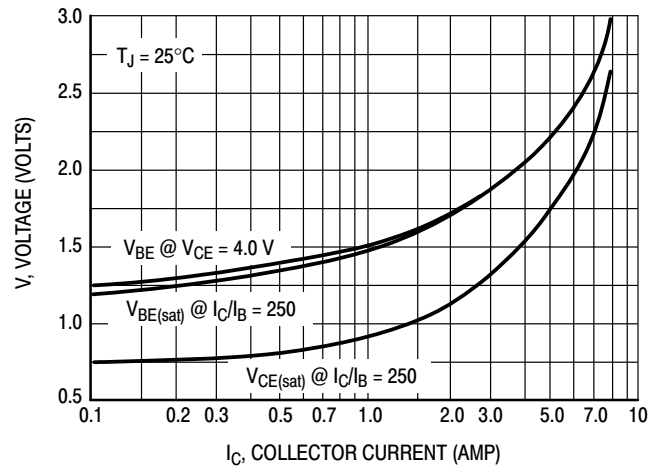
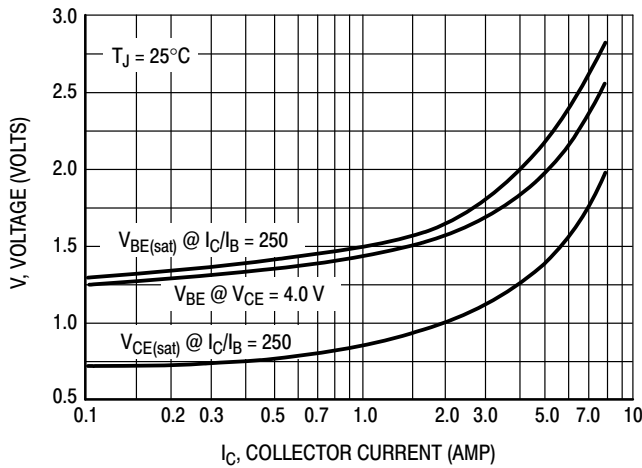
**TIP120, TIP121, TIP122 (NPN); TIP125, TIP126, TIP127 (PNP)**



**Figure 9. DC Current Gain**



**Figure 10. Collector Saturation Region**



**Figure 11. "On" Voltages**

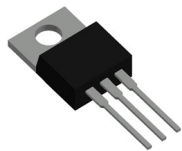


**TIP120, TIP121, TIP122 (NPN); TIP125, TIP126, TIP127 (PNP)****ORDERING INFORMATION**

<b>Device</b>	<b>Package</b>	<b>Shipping</b>
TIP120	TO-220	50 Units / Rail
TIP120G	TO-220 (Pb-Free)	50 Units / Rail
TIP121	TO-220	50 Units / Rail
TIP121G	TO-220 (Pb-Free)	50 Units / Rail
TIP122	TO-220	50 Units / Rail
TIP122G	TO-220 (Pb-Free)	50 Units / Rail
TIP125	TO-220	50 Units / Rail
TIP125G	TO-220 (Pb-Free)	50 Units / Rail
TIP126	TO-220	50 Units / Rail
TIP126G	TO-220 (Pb-Free)	50 Units / Rail
TIP127	TO-220	50 Units / Rail
TIP127G	TO-220 (Pb-Free)	50 Units / Rail

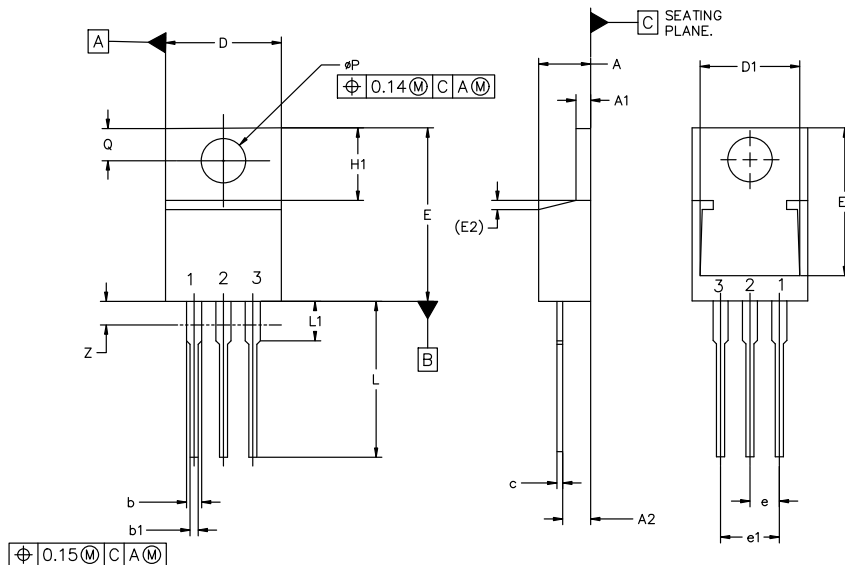


**MECHANICAL CASE OUTLINE**  
**PACKAGE DIMENSIONS**



**TO-220-3 10.10x15.12x4.45, 2.54P**  
**CASE 221A**  
**ISSUE AL**

DATE 05 FEB 2025



$\phi 0.15 \text{ (M) C A (M)}$

MILLIMETERS			
DIM	MIN	NOM	MAX
A	4.07	4.45	4.83
A1	1.15	1.28	1.41
A2	2.04	2.42	2.79
b	1.15	1.34	1.52
b1	0.64	0.80	0.96
c	0.36	0.49	0.61
D	9.66	10.10	10.53
D1	8.43	8.63	8.83
E	14.48	15.12	15.75
E1	12.58	12.78	12.98
E2	1.27 REF		

MILLIMETERS			
DIM	MIN	NOM	MAX
e	2.42	2.54	2.66
e1	4.83	5.08	5.33
H1	5.97	6.22	6.47
L	12.70	13.49	14.27
L1	2.80	3.45	4.10
Q	2.54	2.79	3.04
$\phi P$	3.60	3.85	4.09
Z	---	---	3.48

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

- |                                                                                  |                                                                                |                                                                             |                                                                                                      |
|----------------------------------------------------------------------------------|--------------------------------------------------------------------------------|-----------------------------------------------------------------------------|------------------------------------------------------------------------------------------------------|
| <p>STYLE 1:<br/>PIN 1. BASE<br/>2. COLLECTOR<br/>3. EMITTER<br/>4. COLLECTOR</p> | <p>STYLE 2:<br/>PIN 1. BASE<br/>2. EMITTER<br/>3. COLLECTOR<br/>4. EMITTER</p> | <p>STYLE 3:<br/>PIN 1. CATHODE<br/>2. ANODE<br/>3. GATE<br/>4. ANODE</p>    | <p>STYLE 4:<br/>PIN 1. MAIN TERMINAL 1<br/>2. MAIN TERMINAL 2<br/>3. GATE<br/>4. MAIN TERMINAL 2</p> |
| <p>STYLE 5:<br/>PIN 1. GATE<br/>2. DRAIN<br/>3. SOURCE<br/>4. DRAIN</p>          | <p>STYLE 6:<br/>PIN 1. ANODE<br/>2. CATHODE<br/>3. ANODE<br/>4. CATHODE</p>    | <p>STYLE 7:<br/>PIN 1. CATHODE<br/>2. ANODE<br/>3. CATHODE<br/>4. ANODE</p> | <p>STYLE 8:<br/>PIN 1. CATHODE<br/>2. ANODE<br/>3. EXTERNAL TRIP/DELAY<br/>4. ANODE</p>              |
| <p>STYLE 9:<br/>PIN 1. GATE<br/>2. COLLECTOR<br/>3. EMITTER<br/>4. COLLECTOR</p> | <p>STYLE 10:<br/>PIN 1. GATE<br/>2. SOURCE<br/>3. DRAIN<br/>4. SOURCE</p>      | <p>STYLE 11:<br/>PIN 1. DRAIN<br/>2. SOURCE<br/>3. GATE<br/>4. SOURCE</p>   | <p>STYLE 12:<br/>PIN 1. MAIN TERMINAL 1<br/>2. MAIN TERMINAL 2<br/>3. GATE<br/>4. NOT CONNECTED</p>  |

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